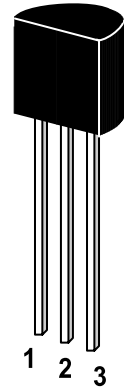


ST 2N6517

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

On special request, these transistors can be manufactured in different pin configurations.



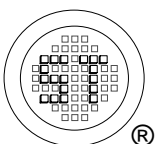
1. Emitter 2. Base 3. Collector

TO-92 Plastic Package

Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	350	V
Collector Emitter Voltage	V_{CEO}	350	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



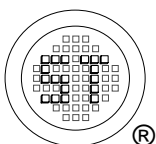
ISO 9001:2000
Certificate No. 0506098

Dated : 07/12/2002

ST 2N6517

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $V_{CE}=10\text{V}$, $I_C=1\text{mA}$	h_{FE}	20	-	-	-
at $V_{CE}=10\text{V}$, $I_C=10\text{mA}$	h_{FE}	30	-	-	-
at $V_{CE}=10\text{V}$, $I_C=30\text{mA}$	h_{FE}	30	-	200	-
at $V_{CE}=10\text{V}$, $I_C=50\text{mA}$	h_{FE}	20	-	200	-
at $V_{CE}=10\text{V}$, $I_C=100\text{mA}$	h_{FE}	15	-	-	-
Collector Base Breakdown Voltage					
at $I_C=100\mu\text{A}$	BV_{CBO}	350	-	-	V
Collector Emitter Breakdown Voltage					
at $I_C=1\text{mA}$	BV_{CEO}	350	-	-	V
Emitter Base Breakdown Voltage					
at $I_E=10\mu\text{A}$	BV_{EBO}	6	-	-	V
Collector Cutoff Current					
at $V_{CB}=250\text{V}$	I_{CBO}	-	-	50	nA
Emitter Cutoff Current					
at $V_{EB}=5\text{V}$	I_{EBO}	-	-	50	nA
Collector Base Capacitance					
at $V_{CB}=20\text{V}$, $f=1\text{MHz}$	C_{cb}	-	-	6	pF
Base Emitter Saturation Voltage					
at $I_C=10\text{mA}$, $I_B=1\text{mA}$	$V_{BE(sat)}$	-	-	0.75	V
at $I_C=20\text{mA}$, $I_B=2\text{mA}$	$V_{BE(sat)}$	-	-	0.85	V
at $I_C=30\text{mA}$, $I_B=3\text{mA}$	$V_{BE(sat)}$	-	-	0.9	V
Collector Emitter Saturation Voltage					
at $I_C=10\text{mA}$, $I_B=1\text{mA}$	$V_{CE(sat)}$	-	-	0.3	V
at $I_C=20\text{mA}$, $I_B=2\text{mA}$	$V_{CE(sat)}$	-	-	0.35	V
at $I_C=30\text{mA}$, $I_B=3\text{mA}$	$V_{CE(sat)}$	-	-	0.5	V
at $I_C=50\text{mA}$, $I_B=5\text{mA}$	$V_{CE(sat)}$	-	-	1	V
Base Emitter On Voltage					
at $V_{CE}=10\text{V}$, $I_C=100\text{mA}$	$V_{BE(on)}$	-	-	2	V
Current Gain Bandwidth Product					
at $V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=20\text{MHz}$	f_T	40	-	200	MHz



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